

COPY OF PAPERS
ORIGINALLY FILED

FEE TRANSMITTAL SHEET (FOR FY 2001)

Complete if Known

Application No. 09/652,579
Filing Date August 31, 2000
First Named Inventor Vishnu K. Agarwal
Group Art Unit 2825
Examiner Caridad M. Everhart
Atty. Docket Number 501082.14 (98-0616.13)

METHOD OF PAYMENT (Check One)

1. ☒ The Commissioner is hereby authorized to charge any additional fee required under 37 C.F.R. §§ 1.16 and 1.17 and 1.136(a)(3) and credit any over payments to Deposit Account No.: 50-1266; Deposit Account Name: DORSEY & WHITNEY LLP

2. ☐ Check Enclosed

FEE CALCULATION

1. BASIC FILING FEE

Large Entity		Small Entity		Fee Description
Fee Code	Fee (\$)	Fee Code	Fee (\$)	
101	740	201	370	<input type="checkbox"/> Utility Filing Fee
106	330	206	165	<input type="checkbox"/> Design Filing Fee
108	740	208	370	<input type="checkbox"/> Reissue Filing Fee
114	160	214	80	<input type="checkbox"/> Provisional Filing Fee

Subtotal (1) \$0

2. EXTRA CLAIM FEES

Current Claims	Prior	Extra	Fee	Fee Paid
Total 6	- 20	= 0	x \$	= \$0
Ind. 2	- 3	= 0	x \$	= \$0
IMultiple Dependent Claims x \$ = \$				

Subtotal (2) \$0

Large Entity		Small Entity		Fee Description
Fee Code	Fee (\$)	Fee Code	Fee (\$)	
103	18	203	9	Claims in excess of 20
102	84	202	42	Independent claims in excess of 3
104	280	204	140	Multiple dependent Claim
109	80	209	40	Reissue independent claims over original patent
110	18	210	9	Reissue claims in excess of 20 and over original patent

FEE CALCULATION (Continued)

3. ADDITIONAL FEES

Large Entity		Small Entity		Fee Description	Fee paid
Fee Code	Fee (\$)	Fee Code	Fee (\$)		
105	130	205	65	Surcharge - Late filing fee or oath	\$
127	50	227	25	Surcharge - late provisional filing fee or cover sheet	\$
139	130	139	130	Non-English specification	\$
147	2,520	147	2,520	For Filing a Request for Reexamination	\$
195	300	196	300	Publication (early or Republication)	\$
115	110	215	55	Extension for reply within first month	\$
116	400	216	200	Extension for reply within 2 nd month	\$
117	920	217	460	Extension for reply within 3 rd month	\$
118	1,440	218	720	Extension for reply within 4 th month	\$
128	1,960	280	980	Extension for reply within 5 th month	\$
120	320	220	160	Filing a brief in support of an appeal	\$
121	280	270	140	Request for oral hearing	\$
148	110	248	55	Terminal Disclaimer Fee	\$
140	110	240	55	Petition to revive - unavoidable	\$
11	1,280	241	640	Petition to revive - unintentional	\$
12	1,280	242	640	Utility/Reissue issue fee (+ advance copies)	\$
14	460	243	230	Design issue fee (+ advance copies)	\$
122	130	122	130	Petitions to the Commissioner	\$
123	50	123	50	Petitions related to provisional applications	\$
126	180	126	180	Submission of IDS	\$
581	40	81	40	Recording each patent assignment per property (times number of properties)	\$
179	740	279	370	Request for Continued Examination (RCE)	\$

Other fee (specify)

Subtotal (3) \$0

Total Amount of Payment: \$0

Submitted by:

Name: Paul F. Rdsyn

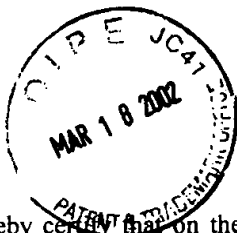
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Signature:

Date:

5 March 02



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#12/Amended
Patent
7/20/02

PATENT

I hereby certify that on the date specified below, this correspondence is being deposited with the United States Postal Service as first-class mail in an envelope addressed to Box Non-Fee Amendment, Commissioner of Patents, Washington, DC 20231.

March 5, 2002

Date

Ayesha S. Wilks

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Vishnu K. Agarwal

Attorney Docket No.: 501082.14 (98-0616.13)

Serial No. : 09/652,579

Group Art Unit : 2825

Filed : August 31, 2000

Examiner : Caridad M. Everhart

Title : DEVICE AND METHOD FOR PROTECTING AGAINST OXIDATION OF A
CONDUCTIVE LAYER IN SAID DEVICE

Box Non-Fee Amendment
Commissioner of Patents
Washington, DC 20231

AMENDMENT

Sir:

Please amend the above-captioned patent application as follows:

In the Claims:

Please cancel claims 45 and 46.

Please amend claims 47 and 48 as follows:

B'

47. (Amended) A method of treating a wafer, comprising:
depositing a first conductive layer onto the wafer;
exposing the wafer in situ to a reducing environment; and
depositing a second conductive layer; and
exposing said wafer in situ to an N₂/H₂ plasma prior to said step
of depositing a second conductive layer.